Please replace the paragraph on page 8, line 22 - page 8, line 3, with the following paragraph:

As illustrated in FIG. 1E, the uncovered areas of the silicon wafer **12e** are etched away in bulk by potassium hydroxide (KOH). Etching the silicon wafer **12e** with potassium hydroxide results in between approximately 50 micrometers and approximately 100 micrometers of the silicon wafer **12e** being exposed. The remaining photoresist **16d** is also removed as illustrated in **FIG. 1F**. Next, as illustrated in **FIG. 1G**, a photoresist coating **18g** is applied to the silicon wafer **12g**. Then, as illustrated in **FIG. 1H**, the silicon wafer **12h** is patterned and exposed and the lancet devices **10h** are "punched" out using a plasma etching process. Plasma etching provides excellent control of the shape of the microlancet without forming weak spots. Finally, as illustrated in **FIG. 1I**, the photoresist coating **18h** is removed resulting in a silicon lancet device with a nitride-covered base.

In the Claims:

Following is a list of all pending claims. Marked up versions of all revised claims, showing insertions and deletions, are included in Appendix B.

Please amend the claims as follows:

24. (Amended) A microlancet device for obtaining a sample of blood or other bodily fluid through the skin of a subject, comprising;

an elongated single crystal silicon substrate having a base end and a penetration end;

a base portion formed at the base end of the silicon substrate for permitting the device to be retained during penetration and sampling; and

a penetration portion formed at the penetration end of the silicon substrate, terminating in a sharp point with smooth continuous cutting profile for easily piercing and

penetrating the skin of the subject in order to obtain a sample of blood or other bodily fluid while inflicting minimum pain on the subject.

25. The device of Claim 24, wherein the penetration portion has a thickness cross-section dimension and a width cross-section dimension, at least one of which tapers toward the penetration end to form the sharp point.

26. The device of Claim 25, wherein the thickness cross-section dimension of the penetration portion extends from about 50 micrometers to about 250 micrometers excluding the sharp point, and the width cross-section dimension of the penetration portion also extends from about 50 micrometers to about 250 micrometers excluding the sharp point.

27. The device of Claim 26, wherein the penetration end of the silicon substrate has a length of from about 1 millimeter to about 3 millimeters.

28. The device of Claim 24, further comprising a silicon nitride film over at least part of the base portion.

29. The device of Claim 28, wherein the silicon nitride film is about 2000 Angstroms thick.

30. The device of Claim 24, wherein the microlancet device is disposable.

31. (New) The device of Claim 25, wherein the width cross-section dimension of the penetration portion terminates in a chisel-shaped point at the penetration end.

32. (New) The device of Claim 24 wherein the penetration portion has a width cross-section that tapers from a larger cross-section dimension at the base end toward a smaller cross-section dimension at the penetration end.

33. (New) The device of Claim 32 wherein the width cross-section dimension of the penetration portion extends from about 250 micrometers to about 50 micrometers, excluding the sharp point.

34. (New) The device of Claim 24 wherein the penetration portion has a thickness cross-section dimension from about 50 micrometers to about 250 micrometers.